

HE8807SG

GaAlAs Infrared Emitting Diodes

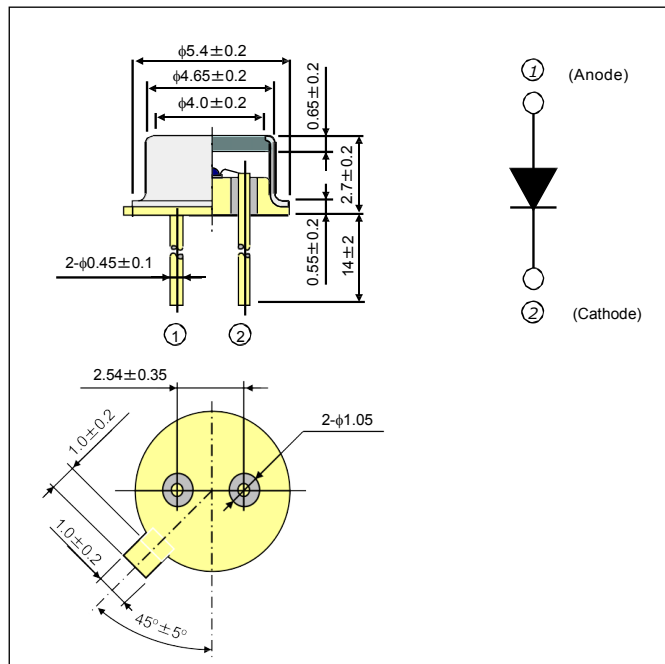
<Specifications>

- Peak Wavelength: 880nm typ.
- High Output, High Efficiency
- Narrow Spectral Width
- Wide Radiation Directivity
- High Reliability

<Application>

- Encoder
- Photoelectric Sensor
- Automatic Apparatus
- Metering Equipment

Outer Dimension (Unit:mm)



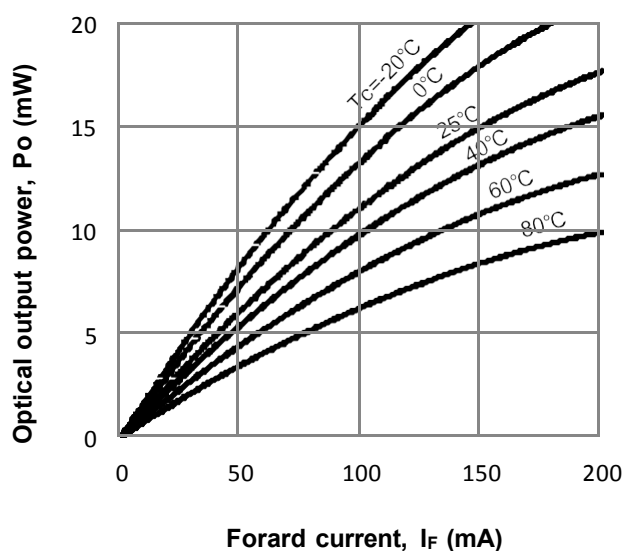
Absolute Maximum Ratings[Tc=25°C]			
Item	Symbol	Ratings	Unit
Forward Current	IF	200	mA
Reverse Voltage	VR	3	V
Operating Temperature	TOPR	-20 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +100	°C

Electro-Optical Characteristics [Tc=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Optical Output Power	Pf*	IF=150mA	10	15		mW
Peak Wavelength	λp	IF=150mA	800	880	900	nm
Spectral Width	Δλ	IF=150mA		30	60	nm
Forward Voltage	VF	IF=150mA		1.7	2.3	V
Reverse Current	IR	VR=3V			100	μA
Capacitance	Ct	VR=0V, f=1MHz		10		pF
Rise Time	tr	IF=50mA		20		ns
Fall Time	tf	IF=50mA		20		ns

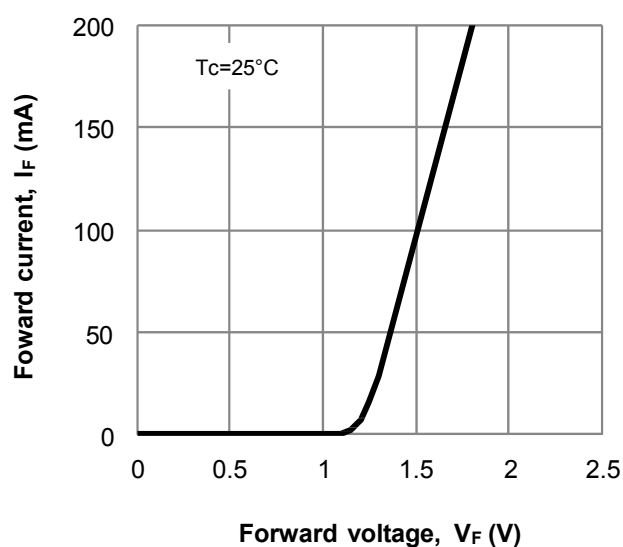


Typical Characteristic Curves

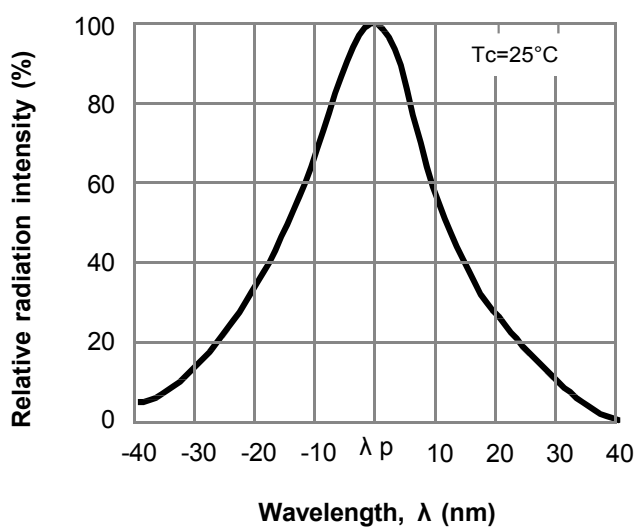
Optical Output Power vs. Forward Current



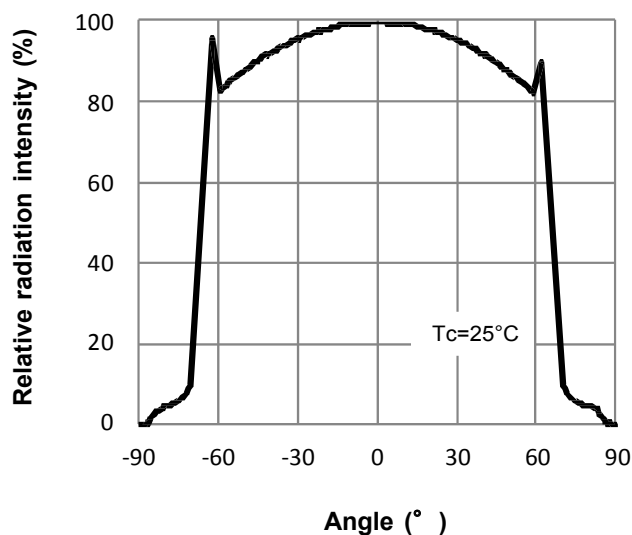
Forward Current vs. Forward Voltage



Wavelength Distribution



Radiation Directional



Disclaimer

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Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

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